

Appl. No. 10/710,596
Amdt. dated March 16, 2007
Reply to Office action of November 16, 2006

REMARKS

The Examiner is thanked for the thorough examination and search of the subject.

5 Paragraph [0001] is amended. No new matter is believed to be added herein.

Claims 43-88 are pending. Claims 43-84 are currently amended. Claims 85-88 are newly added. Claims 1-42 are canceled. No new matter is believed to be added herein.

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Response to Claim Rejections under 35 U.S.C. 112

15 *Reconsiderations of Claim 69 rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention are requested in accordance with the following remarks.*

Withdrawal of rejection to Claim 69 under 35 U.S.C. 112, second paragraph, is requested as Claim 69 is currently amended.

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Response to Claim Rejections under 35 U.S.C. 102 and 103

Applicant respectfully traverses the rejections for at least the reasons set forth below.

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Response to Claims 43-63, 85 and 86

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As currently amended, independent Claim 43 is recited below:

43. A circuit component comprising:

- a semiconductor substrate;
 - a metallization structure over said semiconductor substrate;
 - 5 a silicon-nitride layer over said metallization structure;
 - a circuit trace over said silicon-nitride layer; and
 - a resistor connected to said circuit trace.
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10 *Reconsiderations of Claims 43 and 48-55 rejected under 35 U.S.C. 102(b) as being anticipated by Lin et al. (US 6,495,442), of Claims 44-46 rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. in view of Leidy (US 2003/0155570), of Claims 45 and 47 rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. in view of Simila (US 2003/0183332), and of Claims 54-63 rejected under 35 U.S.C. 103(a) as being*
15 *unpatentable over Lin et al. in view of Carichner et al. (US 5,972,734) are requested in accordance with the following remarks.*

Applicant respectfully asserts that the circuit component claimed in Claim 43 patentably distinguishes over the citations by Lin et al. (US 6,495,442).

20 Lin et al. teach a circuit component comprising a semiconductor substrate 10, a metallization structure 14 over said semiconductor substrate 10, a silicon-nitride layer 18 over said metallization structure 14, and a circuit trace 21. ~ See Fig. 7a; col. 7, line 61 through col. 8, line 6 ~

25 The Examiner considers that Lin et al. teach the circuit component comprises a resistor. ~ See lines 2 and 3, on page 3, in the last Office Action mailed Nov. 16, 2006 ~

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Applicant respectfully traverses the Examiner opinions because Lin et al. fail to teach the circuit component may comprise a resistor. In col. 8, lines 14-19, Lin et al. teach that "It is clear from previous discussions that the sequence of layers that is shown in cross section in FIG. 7a has been created so that additional electrical components such as an inductor, a capacitor and the like can be created on the surface of layer 20 of polyimide and in electrical contact with conductive plugs 21". In the above Lin et al.'s disclosure, Lin et al. fail to teach the circuit component may comprise a resistor, as claimed in Claim 43.

Lin et al. fail to teach that the circuit component may comprise a resistor connected to a circuit trace over a silicon-nitride layer, as claimed in Claim 43.

Withdrawal of rejection under 35 U.S.C.102(b) to Claim 43 is respectfully requested.

For at least the foregoing reasons, applicant respectfully submits independent Claim 43 patently distinguishes over the prior art references, and should be allowed. For at least the same reasons, dependent Claims 44-63, 85 and 86 patently define over the prior art as well.

Response to Claims 64-84, 87 and 88

As currently amended, independent Claim 64 is recited below:

64. A circuit component comprising:
multiple MOS devices;
a metallization structure over said multiple MOS devices;
a passivation layer over said metallization structure;

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a circuit trace over said passivation layer; and
a resistor connected to said circuit trace.

5 *Reconsiderations of Claims 64 and 69-76 rejected under 35 U.S.C. 102(b) as being
anticipated by Lin et al. (US 6,495,442), of Claims 65-67 rejected under 35 U.S.C. 103(a)
as being unpatentable over Lin et al. in view of Leidy (US 2003/0155570), of Claims 66
and 68 rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. in view of
Simila (US 2003/0183332), and of Claims 75-84 rejected under 35 U.S.C. 103(a) as being
10 unpatentable over Lin et al. in view of Carichner et al. (US 5,972,734) are requested in
accordance with the following remarks.*

Applicant respectfully asserts that the circuit component claimed in Claim 64
patentably distinguishes over the citations by Lin et al. (US 6,495,442).

15

Lin et al. teach a circuit component comprising a metallization structure 14, a
passivation layer 18 over said metallization structure 14, and a circuit trace 21. ~ See
Fig. 7a; col. 7, line 61 through col. 8, line 6 ~

20 The Examiner considers that Lin et al. teach the circuit component comprises a
resistor. ~ See lines 2 and 3, on page 3, in the last Office Action mailed Nov. 16, 2006 ~

25 Applicant respectfully traverses the Examiner opinions because Lin et al. fail to
teach the circuit component may comprise a resistor. In col. 8, lines 14-19, Lin et al.
teach that "It is clear from previous discussions that the sequence of layers that is shown
in cross section in FIG. 7a has been created so that additional electrical components such
as an inductor, a capacitor and the like can be created on the surface of layer 20 of
polyimide and in electrical contact with conductive plugs 21". In the above Lin et al.'s

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disclosure, Lin et al. fail to teach the circuit component may comprise a resistor, as claimed in Claim 64.

5 Lin et al. fail to teach that the circuit component may comprise a resistor connected to a circuit trace over a passivation layer, as claimed in Claim 64.

In addition, the Examiner considers that Lin et al. teach the circuit component comprises multiple MOS devices. ~ See lines 1 and 2, in point 5, in the last Office Action mailed Nov. 16, 2006 ~

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Applicant respectfully traverses the Examiner opinions because Lin et al. fail to teach the circuit component may comprise multiple MOS devices. In col. 4, lines 49-51, Lin et al. teach that "The surface of silicon substrate 10 has been provided with transistors and other devices (not shown in FIG. 6)". In the above Lin et al.'s disclosure, Lin et al.
15 fail to teach the circuit component may comprise multiple MOS devices, as claimed in Claim 64.

Lin et al. fail to teach that the circuit component may comprise said metallization structure 14 may be over multiple MOS devices, as claimed in Claim 64.

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Withdrawal of rejection under 35 U.S.C.102(b) to Claim 64 is respectfully requested.

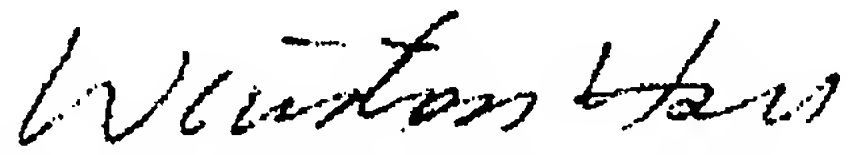
For at least the foregoing reasons, applicant respectfully submits independent
25 Claim 64 patently distinguishes over the prior art references, and should be allowed. For at least the same reasons, dependent Claims 65-84, 87 and 88 patently define over the prior art as well.

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Conclusion

Some or all Claims are believed to be in condition for Allowance, and that is so requested.

5 Sincerely yours,



Date: 03/16/2007

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Note: Please leave a message in my voice mail if you need to talk to me. (The time in D.C.
15 is 12 hours behind the Taiwan time, i.e. 9 AM in D.C. = 9 PM in Taiwan.)